## EE 538B CMOS RF IC DESIGN

Midterm Examination No. 1: April 28, 2004

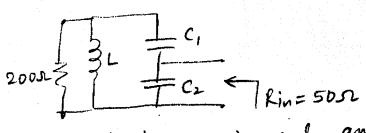
UW Student ID #:_	123430	/ <del>T</del>	· · · · · · · · · · · · · · · · · · ·	· · · · · · · · · · · · · · · · · · ·
UW Student ID #:	12215	.7		
Student Name:	Solutions			

Problem #		Points Possible	Points		
1		10	10		
 2		20	20		
3	- 1	<b>25</b>	25		
4		<b>25</b>	2.5		
5		20	2.0		

100

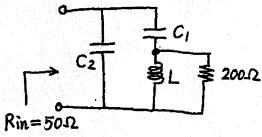
1. (10 points) With Q=10, the matching circuit below is used to convert  $R_L = 200\Omega$  to  $R_{IN} = 50\Omega$  at  $f_0$ = 2.4GHz. Determine the required component values. (Sorry Jeff, No Smith Charts are provided<sup>®</sup>)

can be hedrawn as a ckt tapped capacitor match.



ekt is reciprocal, and

direction is easier.



analysing the

$$\lim_{R \to \infty} \frac{1}{3} \frac{C_1}{C_2} = \lim_{R \to \infty} \frac{1}{3} \frac{C_2}{R_2} = \lim_{R \to \infty} \frac{1}{3} \frac{C_2}{R_2$$

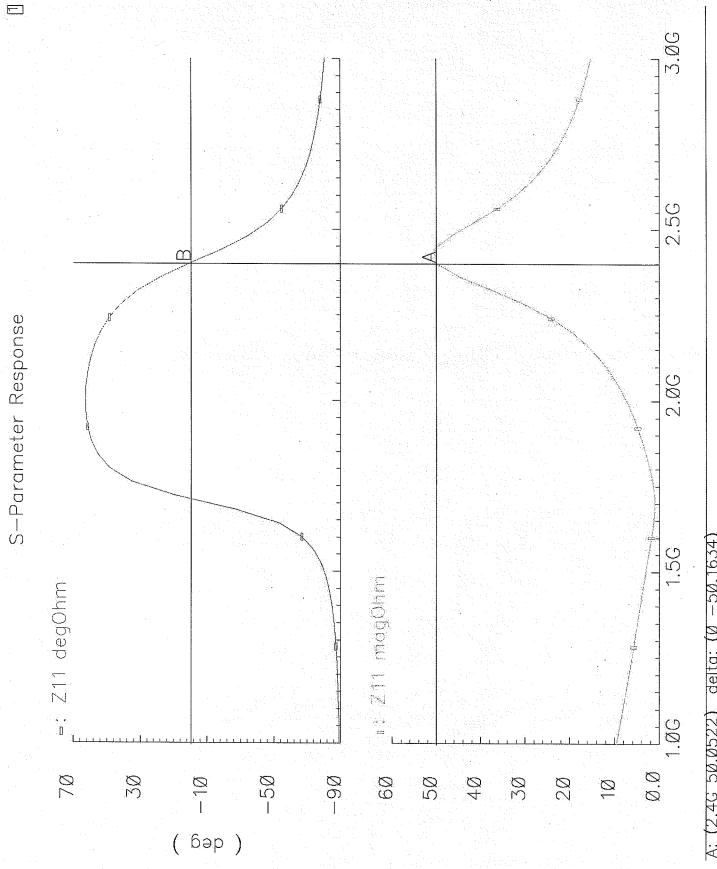
$$C_{\beta} = \frac{R}{\omega_{\delta}R_{\beta}} = 3.316 \, \beta F \Rightarrow C_{S} = 3.35 \, \beta F$$

$$R_{LS} = \frac{RP}{1+Q^2} = 1.98 \Omega$$

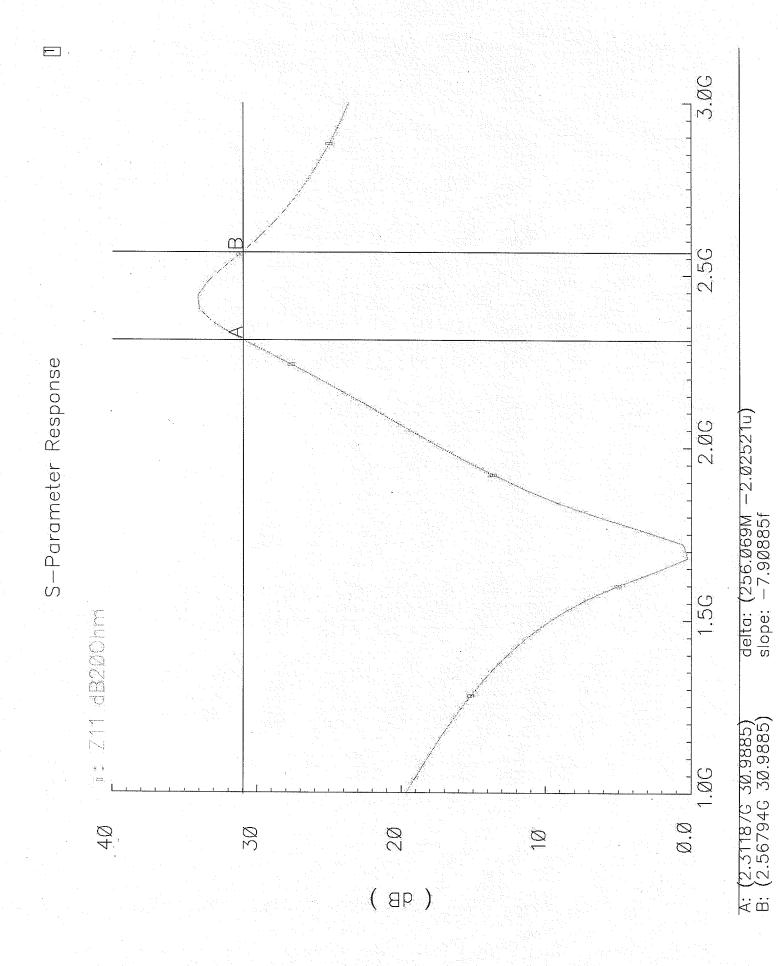
②: 
$$Q_R = \sqrt{\frac{R_L}{R_{Ls}}} - 1 = 4.925$$

$$C_2 = \frac{Q_R}{\omega_s R_L} = \frac{6.53 pF}{6.53 pF} \Rightarrow C_{2s} = 6.8 pF$$

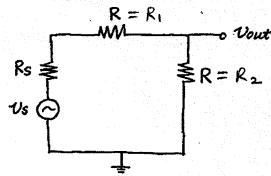
$$\frac{1}{C_s} = \frac{1}{C_1} + \frac{1}{C_{2s}} \Rightarrow C_{1} = \frac{6.60 pF}{6.60 pF}$$



A: (2.4G 50.0522) delta: (0 —50.1634) B: (2.4G —111.149m) slope: undefined



2. (20 points) A resistive network is show below:

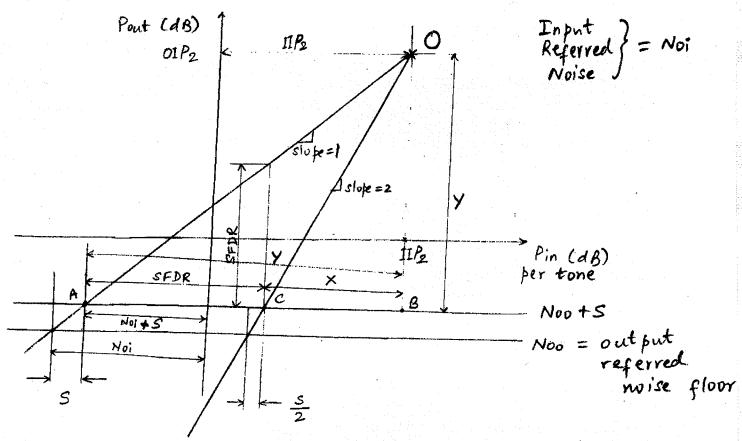


(a) What is the noise factor of the above circuit with respect to source resistance  $R_s$ ?  $\overline{V_{n,R_s}^2} = 4kTR_s \Delta f \cdot \left(\frac{R}{2R+R_s}\right)^2; \quad \overline{V_{n,R_s}^2} = 4kTR \Delta f \left(\frac{R}{2R+R_s}\right)^2$   $\overline{V_{n,R_s}^2} = 4kTR\Delta f \cdot \left(\frac{R+R_s}{2R+R_s}\right)^2$   $NF = \frac{\overline{V_{n,k_s}^2}}{\overline{V_{n,k_s}^2}} = 1 + \frac{\overline{V_{n,R_s}^2}}{\overline{V_{n,R_s}^2}} = 1 + \frac{2R^2 + 2RR_s + R_s^2}{RR_s}$   $= 1 + \frac{4kTR\Delta f \left(\frac{R^2}{(2R+R_s)^2} + \frac{(R+R_s)^2}{(2R+R_s)^2}\right)}{4kTR_s \Delta f \cdot \frac{R^2}{(2R+R_s)^2}} = 1 + \frac{2R^2 + 2RR_s + R_s^2}{RR_s}$   $= 3 + \frac{2R}{R_s} + \frac{R_s}{R_s}$ 

(b) What value of R minimizes the noise factor F?

$$\frac{dNF}{dR} = 0 \implies \frac{2}{Rs} - \frac{Rs}{R^2} = 0 \implies \boxed{R = \frac{Rs}{\sqrt{2}}}$$

3. (25 points) Assume that in a Direct Conversion Receiver (DCR), IIP2 (2<sup>nd</sup> order intermodulation) is the dominant non-linearity component in the system. Determine the relation between SFDR, IIP2 and Input-Referred Noise of the system, using a graphical method. Assume that the system requires a minimum Input SNR 'S' to work properly.



The IM2 curve has a slope of 2; x is the distance between points B&C.

$$\frac{X}{Y} = \frac{1}{2}$$
;  $\frac{X + SFDR}{Y} = 1$  (slope of fundamental wive is 1)

$$X = SFDR = \frac{y}{2}$$

$$Y = x \omega - ord(B) - x \omega - ord(A)$$

$$= IIP_2 - (Noi + S)$$

$$\therefore SFDR = \frac{1}{2} \left[ IIP_2 - Noi - S \right]$$

4. (25 points) Determine the noise factor of the circuit shown below with respect to the source resistance R<sub>S</sub>. Neglect channel length modulation effects, all parasitic capacitors and induced gate noise of the MOSFETs. Assume that all the MOSFETs work in saturation region.

$$\frac{R_{S}}{10 \text{ Nt}_{R_{S}}} = 4 \text{ KT } R_{S} \text{ Af} \left[ \frac{1}{R_{S} + R_{F}} - (g_{m_{1}} + g_{m_{2}}) R_{F}}{R_{S} + R_{F}} \right]^{2} \frac{R_{S}}{R_{S} + R_{F}} \frac{M_{2}}{M_{1}} \frac{V_{OUT}}{I_{N_{1}}} \frac{$$

5. (20 points) Calculate the overall Noise Figure and IIP3 for the RF front end shown below.